

Amendments to the Claims

The current listing of the claims replaces all previous amendments and listings of the claims.

1. (Previously Presented) A ceramic heater comprising:
a ceramic substrate comprising a heating face configured to heat a wafer;
an insulating layer having a thickness of between 0.1 and 1000 μm and a volume resistivity higher than that of said ceramic substrate and disposed on a surface of said ceramic substrate; and

a resistance heating element disposed on an opposite side of the heating face and disposed on said insulating layer.

2. (Original) The ceramic heater according to claim 1,
wherein said ceramic substrate comprises a carbide ceramic or a nitride ceramic and said insulating layer comprises an oxide ceramic.

3. and 4. (Canceled)

5. (Previously Presented) The ceramic heater according to claim 1,
wherein the volume resistivity of said insulating layer is at least 10 times the volume resistivity of said ceramic substrate.

6. (Previously Presented) A ceramic heater comprising;
a ceramic substrate comprising a heating face, the ceramic substrate warped in one direction;

a supporting pin disposed in the heating face; and
a resistance heating element disposed on a surface of said ceramic substrate and disposed on an opposite side of the heating face.

7.-30. (Canceled)

31. (Previously Presented) The ceramic heater according to claim 1,

wherein the insulating layer has a thickness between 1 and 1000 μm .

32. (Previously Presented) The ceramic heater according to claim 1,

wherein a supporting pin is disposed in the heating face.

33. (Previously Presented) The ceramic heater according to claim 1, further

comprising:

means for holding a silicon wafer between 50 and 2000 μm from the heating face and for heating the silicon wafer.

34. (Previously Presented) The ceramic heater according to claim 1,

wherein the ceramic substrate comprises a carbide ceramic or a nitride ceramic.

35. (Previously Presented) The ceramic heater according to claim 32,

wherein the supporting pin comprises a tip having a spired form or a semicircular form.

36. (Previously Presented) The ceramic heater according to claim 6,

wherein the ceramic substrate is warped between 20 and 100 μm .

37. (Currently Amended) The ceramic heater according to claim 6,

wherein the ceramic substrate is warped greater than 25 μm and less than or equal to 100 μm .

38. (Previously Presented) The ceramic heater according to claim 6, further

comprising:

means for holding a silicon wafer between 50 and 2000 μm from the heating face and for heating the silicon wafer.